

Features

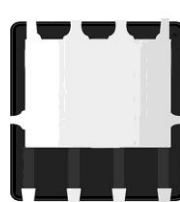
- High density cell design for ultra low $R_{DS(ON)}$
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high EAS

Product Summary

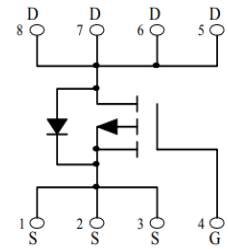
V_{DS}	$R_{DS(ON)}$ TYP	I_D
-40V	9mΩ@-10V	-40A
	12mΩ@-4.5V	

Application

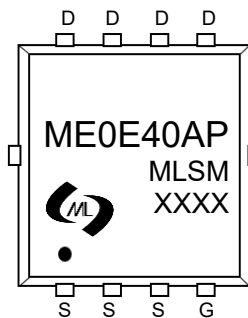
- Battery and loading switching
- Excellent package for good heat dissipation



PDFN3X3-8L view



Schematic diagram



ME0E40AP: Device code
 XXXX: Code

Marking and pin assignment



Halogen-Free

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Rating	Unit
Common Ratings (TC=25°C Unless Otherwise Noted)			
V_{DS}	Drain-Source Breakdown Voltage	-40	V
V_{GS}	Gate-Source Voltage	±20	V
T_J	Maximum Junction Temperature	150	°C
T_{STG}	Storage Temperature Range	-55 to 150	°C
I_S	Diode Continuous Forward Current	$T_c=25^{\circ}C$ -40	A

Mounted on Large Heat Sink

I_{DM}	Pulse Drain Current Tested	$T_c=25^{\circ}C$ -150	A
I_D	Continuous Drain Current	$T_c=25^{\circ}C$ -40	A
P_D	Maximum Power Dissipation	$T_c=25^{\circ}C$ 50	W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient	125	°C/W
E_{AS}	Single pulse avalanche energy ^{Note1}	150	mJ

Ordering Information (Example)

Type	Package	Marking	Minimum Package(pcs)	Inner Box Quantity(pcs)	Outer Carton Quantity(pcs)	Delivery Mode
ME0E40AP	PDFN3X3-8L	ME0E40AP	5,000	10,000	70,000	13"reel

Electrical Characteristics (TJ=25°C unless otherwise noted)						
Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
BV _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250μA	-40	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-40V, V _{GS} =0V	--	--	-1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V	--	--	±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250μA	-1.1	-1.6	-2.5	V
R _{DS(on)}	Drain-Source On-State Resistance	V _{GS} =-10V, I _D =-20A	--	9	13	mΩ
		V _{GS} =-4.5V, I _D =-15A	--	12	20	mΩ
Dynamic Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
C _{ISS}	Input Capacitance	V _{DS} =-30V, V _{GS} =0V, f=1MHz	--	2840	--	pF
C _{OSS}	Output Capacitance		--	213	--	pF
C _{RSS}	Reverse Transfer Capacitance		--	179	--	pF
Switching Characteristics						
Q _g	Total Gate Charge	V _{DD} =-15V, I _D =-20A, V _{GS} =-10V	--	55	--	nC
Q _{gs}	Gate Source Charge		--	9.1	--	nC
Q _{gd}	Gate Drain Charge		--	10.2	--	nC
t _{d(on)}	Turn-on Delay Time	V _{DD} =-15V, I _D =-20A, V _{GS} =-10V, R _G =2.5Ω	--	12	--	nS
t _r	Turn-on Rise Time		--	20	--	nS
t _{d(off)}	Turn-Off Delay Time		--	48	--	nS
t _f	Turn-Off Fall Time		--	20	--	nS
Source- Drain Diode Characteristics						
V _{SD}	Forward on voltage	Tj=25°C, Is=-20A	--	--	-1.2	V

Note :

1、EAS Test condition : V_{DD}=-20V,V_{GS}=10V,L=0.5mH,R_G=25Ω,Starting T_J=25° C.

Typical Operating Characteristics

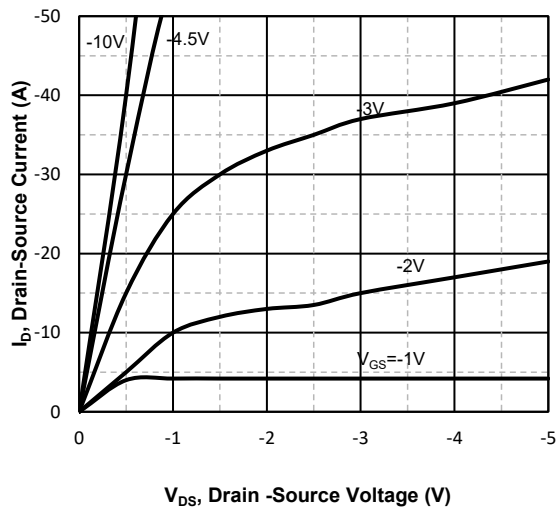


Fig1. Typical Output Characteristics

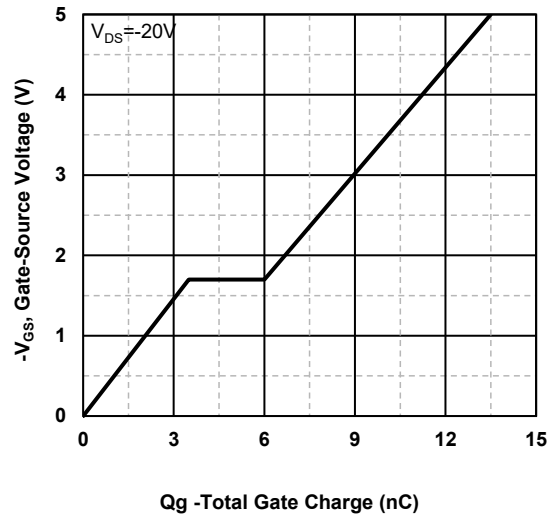


Fig2. Typical Gate Charge Vs. Gate-Source Voltage

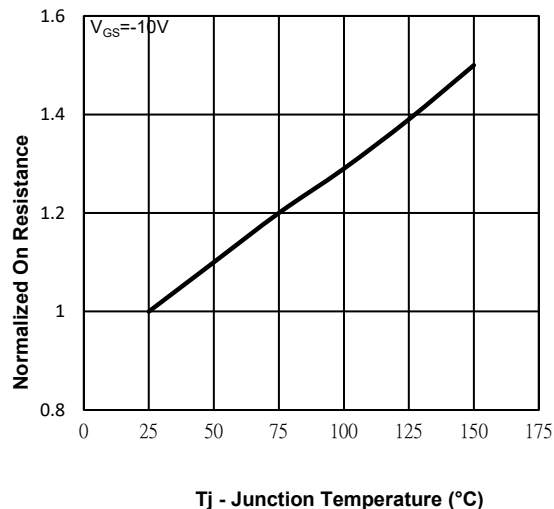


Fig3. Normalized On-Resistance Vs. Temperature

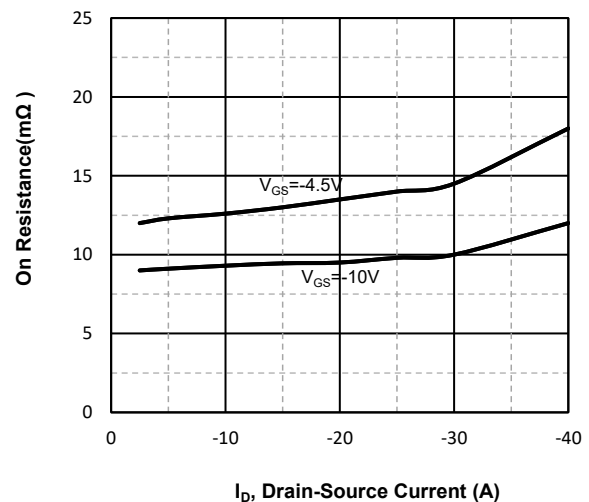


Fig4. On-Resistance Vs. Drain-Source Current

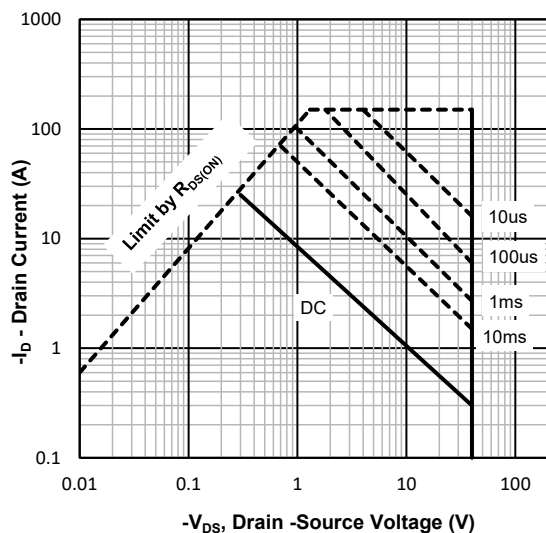


Fig5. Maximum Safe Operating Area

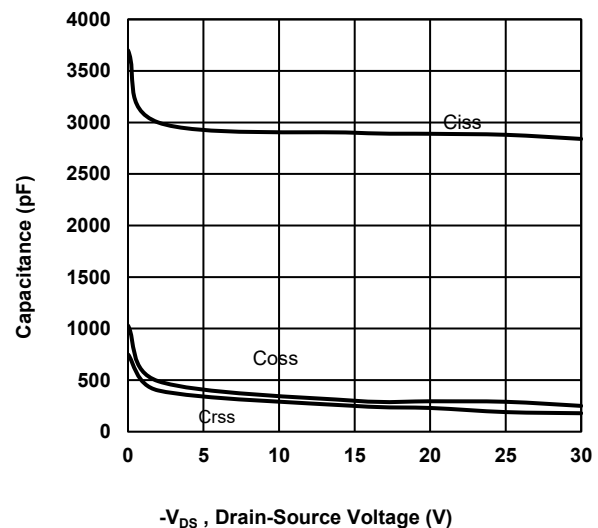
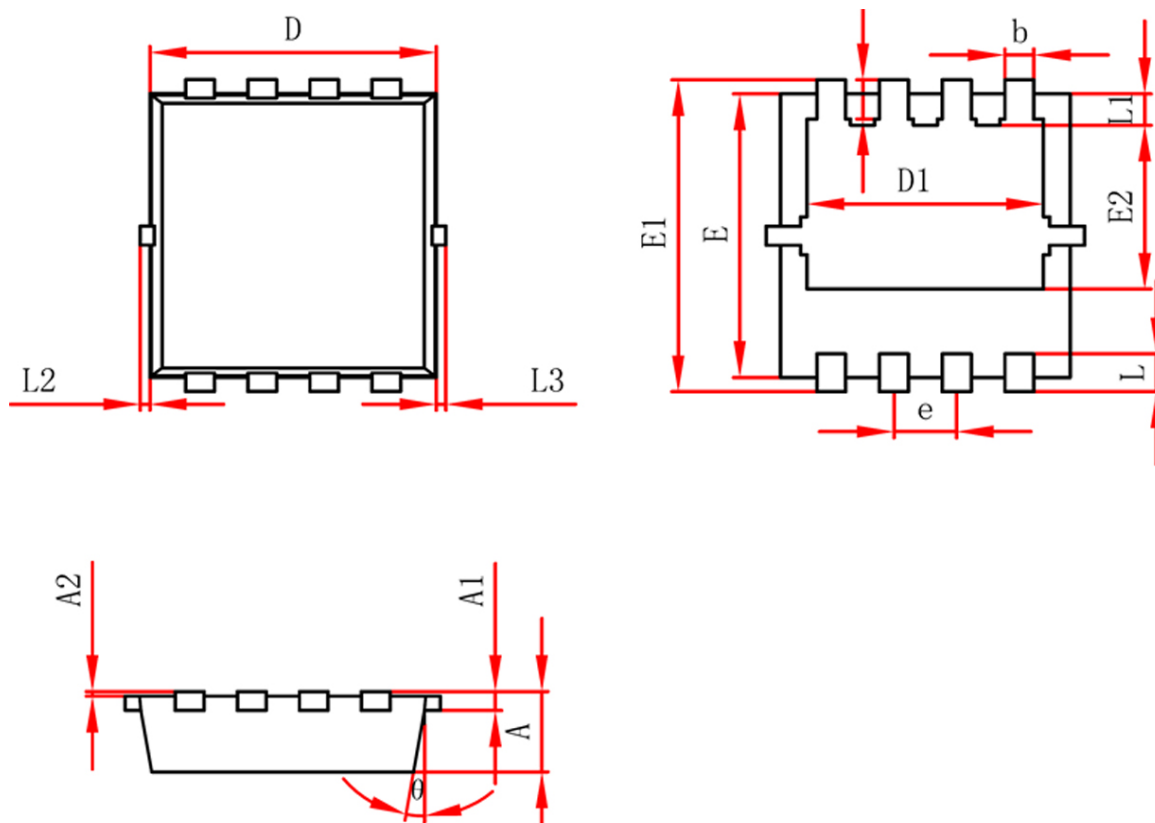


Fig6 Typical Capacitance Vs. Drain-Source Voltage

PDFN3X3-8L Package information



Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	0.750	0.850	0.030	0.034
A1	0.152 REF.		0.006 REF.	
A2	0~0.05		0~0.002	
D	2.950	3.150	0.117	0.125
D1	2.400	2.500	0.095	0.099
E	2.950	3.050	0.117	0.121
E1	3.250	3.350	0.129	0.132
E2	1.685	1.785	0.067	0.071
b	0.250	0.350	0.010	0.014
e	0.600	0.700	0.024	0.028
L	0.350	0.450	0.014	0.018
L1	0.325	0.425	0.013	0.017
L2	0~0.100		0~0.004	
L3	0~0.100		0~0.004	
H	0.365	0.465	0.014	0.018
θ	10°	12°	10°	12°